

# Interleaved PFC Power Supply Basic Simulation Circuit Reference Guide

RD032-RGUIDE-02

**TOSHIBA ELECTRONIC DEVICES & STORAGE CORPORATION** 



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# 1. Introduction

Ideally, the voltage and current waveforms of alternating power are completely sinusoidal and in phase with each other. However, when an AC power supply is connected to a system, its voltage and current waveforms may go out of phase or become non-sinusoidal. A power factor represents the offset in time between the voltage and the current and is defined by following equations:

Power factor = Active power ÷ Apparent power

Active power is the actual power consumed by the load and can be calculated as an integral of instantaneous power (i.e., instantaneous voltage times instantaneous current) over an AC cycle. Apparent power is the product of the rms values of the input voltage and current.

The power factor takes a value between 0 and 1. A power factor of 1 represents the ideal situation where apparent power is equal to active power. A power factor of 0 indicates that apparent power is equal to reactive power. A load with a low power factor draws more apparent power than a load with a high power factor for the same amount of active power transferred. A load with a low power factor is undesirable because it affects other systems and transmission and distribution equipment. Conventional AC-DC power supplies use a diode bridge and a capacitor. In these power supplies, an AC input is rectified to a varying DC voltage, which in turn is converted to a desired voltage. AC-DC power supplies have a pulsed input current since the capacitor is charged only when the capacitor output voltage falls below the output voltage of the diode bridge. Therefore, AC-DC power supplies have a low power factor. Figure 1.1 shows an example of a diode bridge rectifier with a capacitor filter. Figure 1.2 and Figure 1.3 show its waveforms.

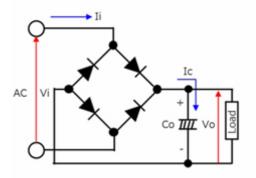


Figure 1.1 Diode bridge rectifier with a capacitor filter

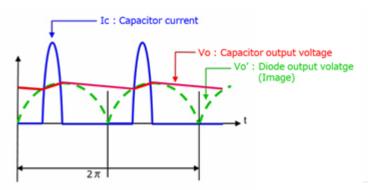


Figure 1.2 Waveforms at different nodes in the circuit

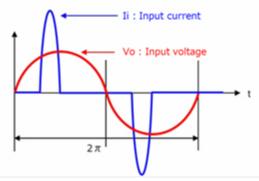


Figure 1.3 Input current and voltage waveforms



The aim of a power factor correction (PFC) circuit is to improve the power factor for AC-DC converters. At present, commonly used AC-DC power supplies incorporate a PFC circuit to improve their power factor. Typically, the PFC circuit in an AC-DC power supply is a boost converter in which an AC input is placed after a diode bridge. Figure 1.4 shows a diode bridge rectifier with a capacitor filter whereas Figure 1.5 shows a boost PFC converter.

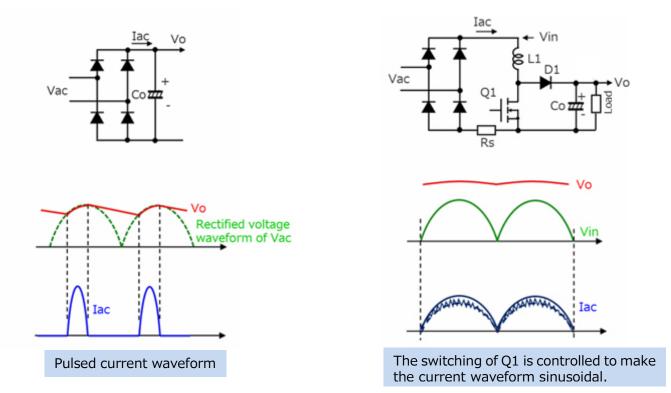
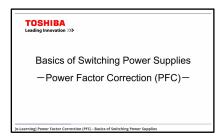


Figure 1.4 Diode bridge rectifier with a capacitor filter

Figure 1.5 Boost PFC converter

A <u>video</u> describing the power factor of an AC-DC power supply and a PFC circuit is on Toshiba's website.



In contrast to a single-phase PFC power supply, a two-phase interleaved PFC power supply consists of two boost converters (comprised of an inductor, a diode, and a MOSFET), which are connected in parallel with 180-degree phase shift between them. Since current flows through two phases, an interleaved PFC power supply can use devices with smaller power ratings than a single-phase PFC power supply with an equal output power. In addition, since two boost converters are 180 degrees out of phase with each other, the combined ripple current from the interleaved PFC power supply is less than a ripple current from the single-phase PFC power supply. Therefore, interleaved PFC is



used for AC-DC power supplies with relatively high output power. A basic simulation circuit of an interleaved PFC power supply (RD032-SPICE-02) is available on Toshiba's website, which will help you understand its operation.

This Reference Guide provides an overview of this simulation circuit and describes its usage. OrCAD<sup>®</sup> Capture and PSpice<sup>®</sup> A/D from Cadence are necessary to simulate this circuit. Both the simulation circuit and the Reference Guide are based on OrCAD<sup>®</sup> 17.2.



# 2. Overview of the PFC power supply

RD032-SPICE-02 is an interleaved PFC power supply with a 1200W output.

#### 2.1. Specifications

The specifications of the interleaved PFC power supply are as follows:

Input voltage: 90 to 264 V<sub>rms</sub>

Output voltage: 400 VOutput current: 0 to 3.0 AOperating frequency: 50 kHz

Allowable peak-to-peak ripple current: 50 % of the peak input current

Inductance setting: 180 µH

#### 2.2. Circuit configuration

Figure 2.1 shows the simulation circuit for OrCAD<sup>®</sup>. It is a continuous-current-mode (CCM) interleaved PFC power supply, which mainly consists of three sections: a power supply section at the upper portion, a PFC controller at the lower portion, and the PARAMETERS section on the right-hand side. The PFC controller is a general-purpose controller with a MOSFET gate driver, which was prepared to create this PFC power supply. The simulation circuit uses the TK20N60W and TRS6E65F as example of switching MOSFETs and diodes.

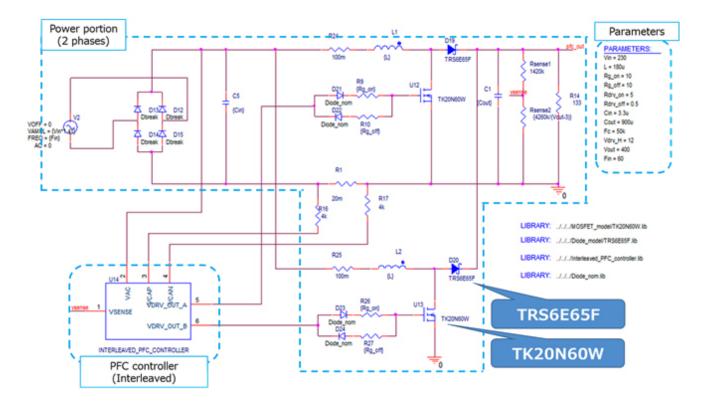


Figure 2.1 Simulation circuit of a 1200W interleaved PFC power supply



#### Selection of the MOSFET and diode

The MOSFET and diode were selected, taking the following into consideration:

(1) Withstand voltage

In the steady state, the MOSFET and diode conduct the same voltage as the output voltage (400V) of the PFC power supply. Therefore, a MOSFET and diode with a withstand voltage of 600V or higher were selected for the simulation circuit.

(2) Current rating

The PFC power supply has the maximum input current when the output power has the maximum value and the input voltage has the minimum value. Suppose that PFC power supply has a conversion efficiency of 94% and a power factor of 1 at the maximum output power of 1200W. Then, the maximum input current is calculated to be roughly  $14.1A_{rms}$  at the minimum input voltage of  $90V_{rms}$ . It is divided into 2 phases.

Assuming a 50% duty cycle, a current of roughly 3.6  $A_{rms}$  is applied to each device. Therefore, a MOSFET and diode with a current rating of 5A or higher were selected for the simulation circuit.

MOSFET: TK20N60W ( $V_{DS}$ =600V /  $I_{D}$ =20A /  $R_{DS(ON)}$ =155m $\Omega$ (Max)

Diode: TRS6E65F (650V/6A)

#### Selection of the inductor

The following paragraphs describe how to select an inductor. The value of the inductor to be used in the simulation circuit can be calculated from the following power supply parameters:

Maximum output power: Pout (W)

Minimum AC line input voltage: V<sub>in\_min</sub> (V<sub>rms</sub>)

PFC power conversion efficiency: n (%)

PFC output voltage: V<sub>out</sub> (V)

Switching frequency: F<sub>c</sub> (Hz)

Allowable peak-to-peak ripple current: ΔI<sub>ripple</sub> (%)

Inductance is calculated by following an equation:

$$L = \frac{\left(V_{out} - \sqrt{2} \times V_{in\_min}\right) \times \eta \times 0.01 \times V_{in\_min}^{2}}{F_{c} \times 0.01 \times \Delta I_{ripple} \times P_{out} \times V_{out}}$$

where, the maximum output power ( $P_{out}$ ) is 1200W, the minimum AC line input voltage ( $V_{in\_min}$ ) is 90V, the PFC output voltage is 400V, and the switching frequency ( $F_c$ ) is 50kHz. Suppose that the PFC power conversion efficiency ( $\eta$ ) is 94%. Then, inductance (L) is calculated to be 173 $\mu$ H. Therefore, inductance is set to 180 $\mu$ H in the simulation circuit.

In practice, the value of the inductor varies because of DC bias characteristics. Select an inductor that exhibits an inductance greater than the result of the above equation even when the inductance decreases because of DC bias characteristics.



The combined ripple current from the interleaved PFC power supply is less than the ripple current that flows through the inductor in each phase. The interleaved PFC power supply can use an inductor with a smaller value to achieve the same current ripple as for a single-phase PFC power supply. However, since a reduction in current ripple varies with operating conditions, sufficient verification is necessary.

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# 3. Simulation results

This section describes the results of the operation of each section of the simulation circuit. The following shows the waveforms of "input voltage and current", "inductor current", "output voltage and current", "MOSFET gate voltage", and "MOSFET drain-source voltage and current" highlighted in Figure 3.1 The simulation circuit model also allows you to view other waveforms. See Section 5 for how to view waveforms.

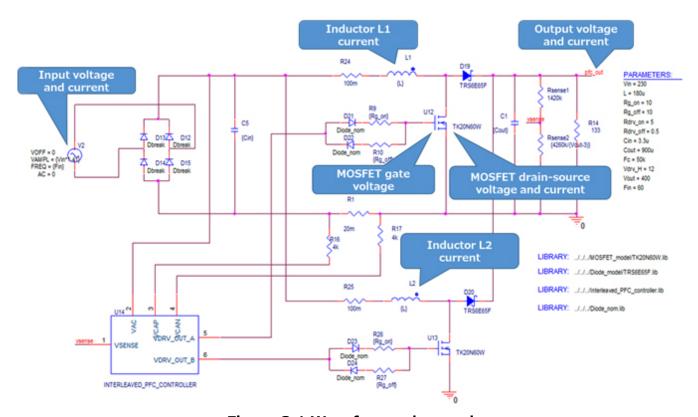


Figure 3.1 Waveforms observed



#### Input voltage and current, output voltage and current, and inductor current waveforms

Figure 3.2, Figure 3.3, and Figure 3.4 show the waveforms of the AC input voltage and current, the PFC output voltage and current, and the inductor current. The output voltage waveform (at the top of Figure 3.2 to 3.4) shows that the PFC output is regulated at 400V as required by the power supply specification. The AC input current waveform (at the middle of Figure 3.2 to 3.4) shows it is sinusoidal, increasing the power factor. The each phase inductor current waveform (at the bottom of Figure 3.4) shows that phase difference of each phase current is 180-degree as interleaved operation.

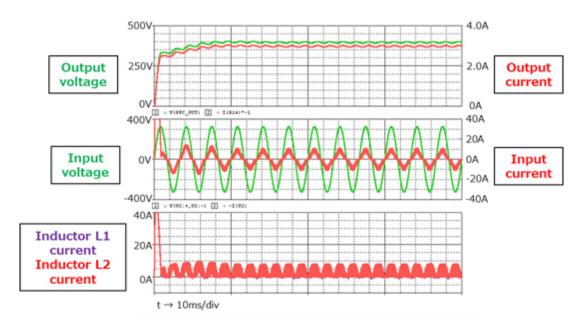


Figure 3.2 Input voltage and current, output voltage and current, and inductor current waveforms

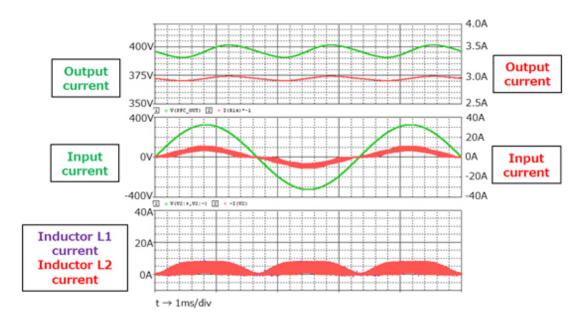


Figure 3.3 Input voltage and current, output voltage and current, and inductor current waveforms (enlarged view 1)



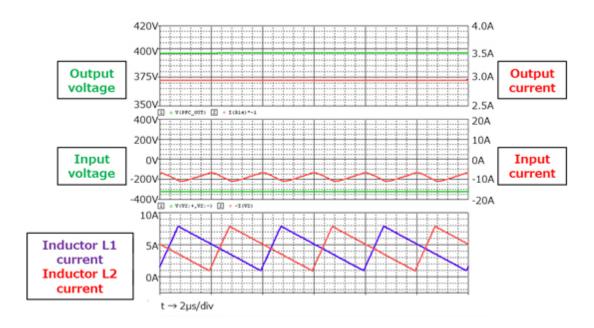


Figure 3.4 Input voltage and current, output voltage and current, and inductor current waveforms (enlarged view 2)



#### MOSFET gate voltage and MOSFET drain-source voltage and current waveforms

Figure 3.5 shows the waveforms of the gate voltage of the TK20N60W, which is used as a switching MOSFET in the simulation circuit. Figure 3.6 shows the waveforms of the drain-source voltage ( $V_{DS}$ ) and current ( $I_D$ ). The MOSFET is PWM-controlled to generate a half-sinusoidal inductor current. Figure 3.5 and Figure 3.6 show the MOSFET waveforms at the point in time when the inductor current has reached the peak value.

In the simulation circuit, parameters Rg\_on and Rg\_off are used to specify the parameters of an external resistor connected to the MOSFET Gate. You can verify the effect of the gate resistance on the behavior of the MOSFET by changing these parameters.

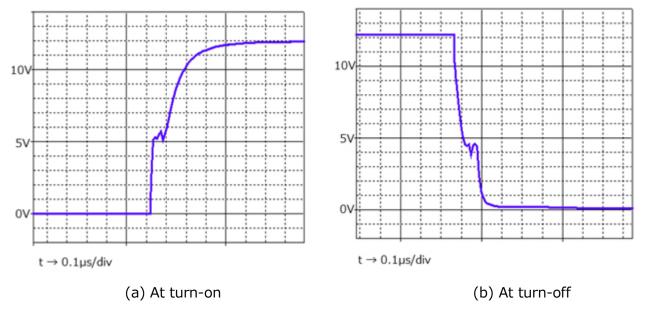


Figure 3.5 MOSFET gate voltage waveforms

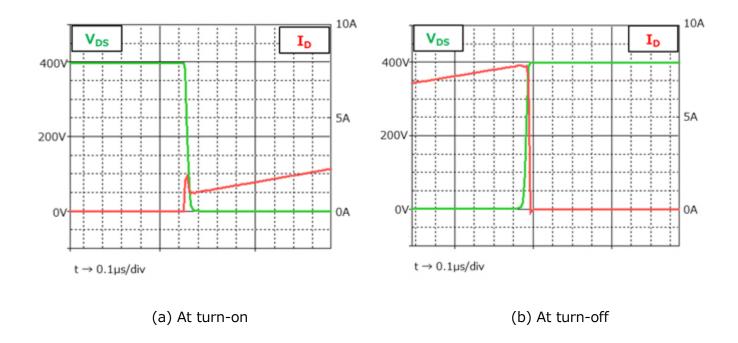


Figure 3.6 MOSFET drain-source voltage and current waveforms



# 4. Product overview

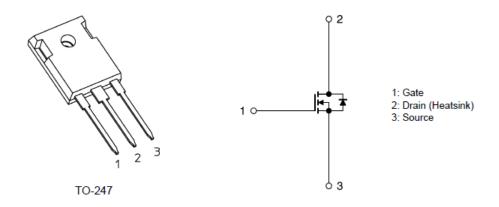
This section provides an overview of Toshiba's devices used as PSpice<sup>®</sup> models in the simulation circuit.

#### 4.1. TK20N60W

#### **Features**

- Low drain-source on-resistance due to a super-junction DTMOS process:  $R_{DS(ON)} = 130 m\Omega$  (Typ)
- Optimized gate switching speed
- Easy-to-use enhanced-mode MOSFET:  $V_{th} = 2.7$  to 3.7V ( $V_{DS} = 10V$ ,  $I_D = 1$ mA)

#### Package and Pin assignment

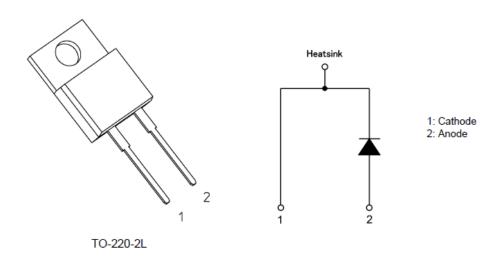


#### 4.2. TRS6E65F

#### **Features**

- High surge current capability: I<sub>FSM</sub> = 55A (Max)
- Low junction capacitance:  $C_j = 22pF$  (Typ.)
- Low leakage current:  $I_R = 0.3 \mu A$  (Typ.)

#### Package and Pin assignment



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### 5. Simulation circuit

You can freely change various parameters with OrCAD<sup>®</sup> Capture to verify the circuit operation according to the actual power supply specifications and evaluate how these parameters affect the circuit operation. This section describes how to set parameters and verify the circuit operation. This simulation circuit appears, when the OPJ file (.opj) inside the folder of RD032-SPICE-02 is opened.

#### **Parameter Settings**

Table 5.1 lists the adjustable parameters which is possible to you can set for the simulation circuit. Double-click a parameter name in the PARAMETERS section. Then, the Display Properties dialog box appears as shown in Figure 5.1. Change the value in the Value field.

lable 3.1 Adjustable rarameters list on the rarameters section				
Parameter	Unit	Description		
Vin	$V_{rms}$	AC input voltage		
Fin	Hz	AC input frequency		
Vout	V	PFC output voltage		
L	Н	Boost inductor parameter		
DCR	Ω	Inductor parasitic resistance		
Cin	F	Input capacitor parameter		
Cout	F	Output capacitor parameter		
Fc	Hz	Switching frequency		
Rg_on	Ω	External gate resistor value for turn-on		
Rg_off	Ω	External gate resistor value for turn-off		
Rdrv_on	Ω	Gate driver internal resistor for turn-on		
Rdrv_off	Ω	Gate driver internal resistor for turn-off		
Vdrv_H	V	Supply voltage of the gate driver		

Table 5.1 Adjustable Parameters List on the Parameters section

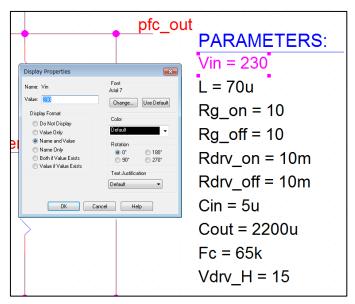


Figure 5.1 Display Properties dialog box



#### **Analysis Setting**

The following describes how to run a simulation on the simulation circuit.

1. From the menu bar of OrCAD<sup>®</sup> Capture, select **PSpice** - **New Simulation Profile**. Then, the New Simulation dialog box shown in Figure 5.2 appears. Enter an arbitrary profile name and click **Create**.

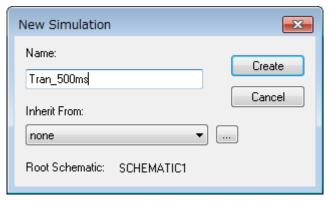


Figure 5.2 New Simulation dialog box

2. Then, the Simulation Settings dialog box shown in Figure 5.3 appears. In this dialog box, you can set parameters for various types of analysis. First, click the **Analysis** tab. Select **Time Domain (Transient)** from the **Analysis Type** drop-down list. Enter the simulation end time in the **Run To Time** field and the maximum step size in the **Maximum Step Size** field.

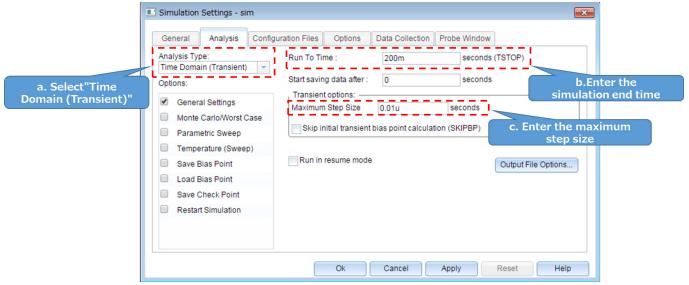


Figure 5.3 Simulation Settings - Analysis dialog box

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3. Click the **Options** tab to choose analysis options. For the simulation of our model, it is recommended to check **Analog Simulation** - **Auto Converge** - **AutoConverge** as shown in Figure 5.4 to enable the automatic convergence feature.

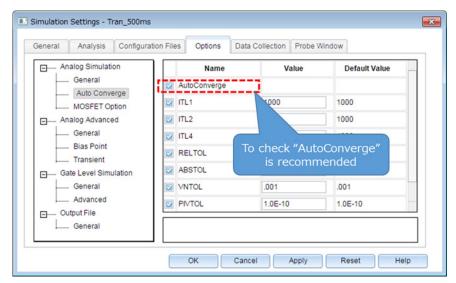


Figure 5.4 Simulation Settings - Options dialog box

- 4. Click **OK** to close the Simulation Settings dialog box.
- 5. To run a simulation, select **PSpice Run** from the menu bar of OrCAD Capture. Then, PSpice A/D starts automatically and runs a simulation.

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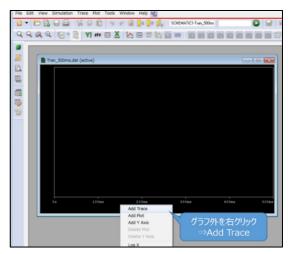


#### **Viewing simulation results**

The following describes how to view the simulation results. You can display the waveforms of the simulation results in two ways.

#### **Method 1: Selecting traces**

- 1. Right-click outside the graph area and select **Add Trace** as shown in Figure 5.5.
- 2. Then, the Add Traces dialog box shown in Figure 5.6 appears. Select traces to be added to a selected plot. To view a voltage waveform, select V(*trace\_name*). To view a current waveform, select I(*device\_name*).
- 3. Click **OK**. Then, the selected waveform appears as shown in Figure 5.7.



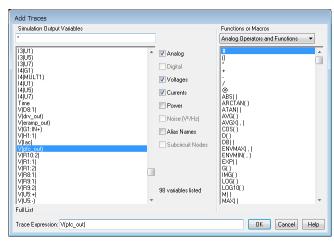


Figure 5.5 Graph window Figure 5.6 Add Traces dialog box

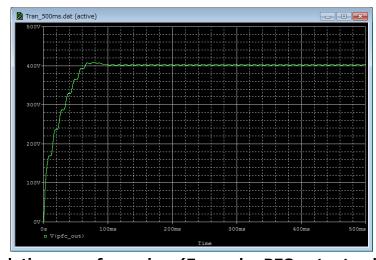


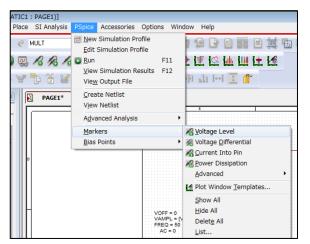
Figure 5.7 Simulation waveform view (Example: PFC output voltage waveform)

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#### Method 2 Adding markers

- 1. From the menu bar of OrCAD<sup>®</sup> Capture, select **PSpice Markers** and then a type of marker as shown in Figure 5.8.
- 2. Place the selected marker on the desired node in the simulation circuit as shown in Figure 5.9.
- 3. Then, its waveform appears in the graph window of PSpice® A/D as shown in Figure 5.10.



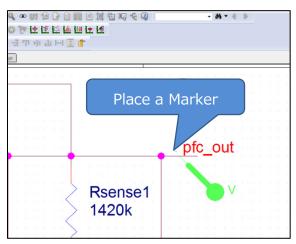


Figure 5.8 Selecting a marker type Figure 5.9 Placing a marker in the circuit

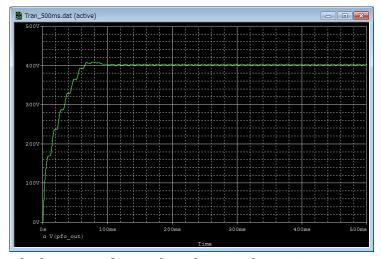


Figure 5.10 Simulation waveform view (Example: PFC output voltage waveform)

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